

# SURFACE PROPERTY MODIFICATION OF SEMICONDUCTORS BY FLUID ABSORPTION

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## Objectives

- . Lubricated Cutting (wafering)  
laboratory simulation  
mechanism  
model
- . Residual Stresses in Sheet  
Develop Interferometry Technique  
Apply to EFG and WEB

## Lubricated Cutting in Simulated Laboratory Experiments

|                           |                    |
|---------------------------|--------------------|
|                           | Surface Morphology |
|                           | Hardness           |
| Load, Temperature, Fluids | Wear rate          |
|                           | Depth of Damage    |

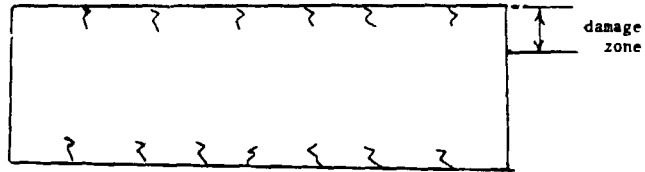
Mechanism

Model

# ADVANCED SILICON SHEET

## Silicon Wafer

cracks (propagate on  
cleavage planes)



plasticity(?)  
. due to high compressive stresses  
. at crack tips

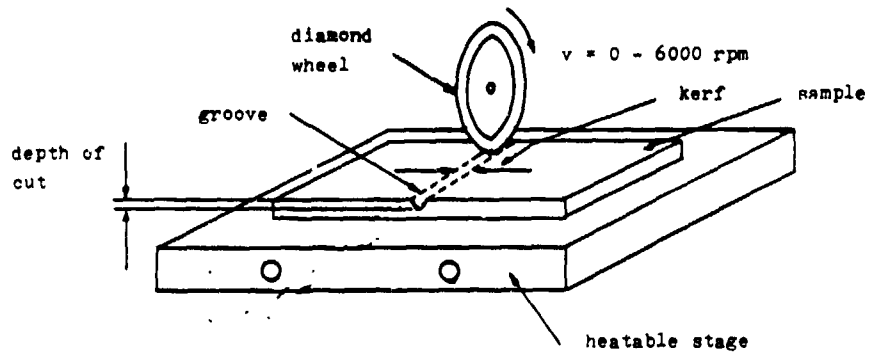
. Simulate Damage

dicing (OD sawing)

indentation (Vickers dia)

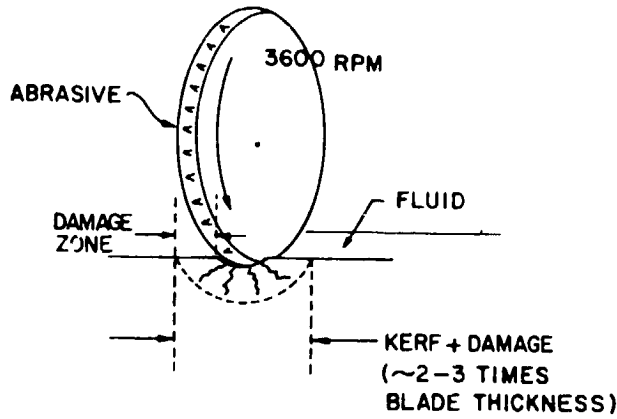
Identify critical parameters

Load  
fluid  
temperature

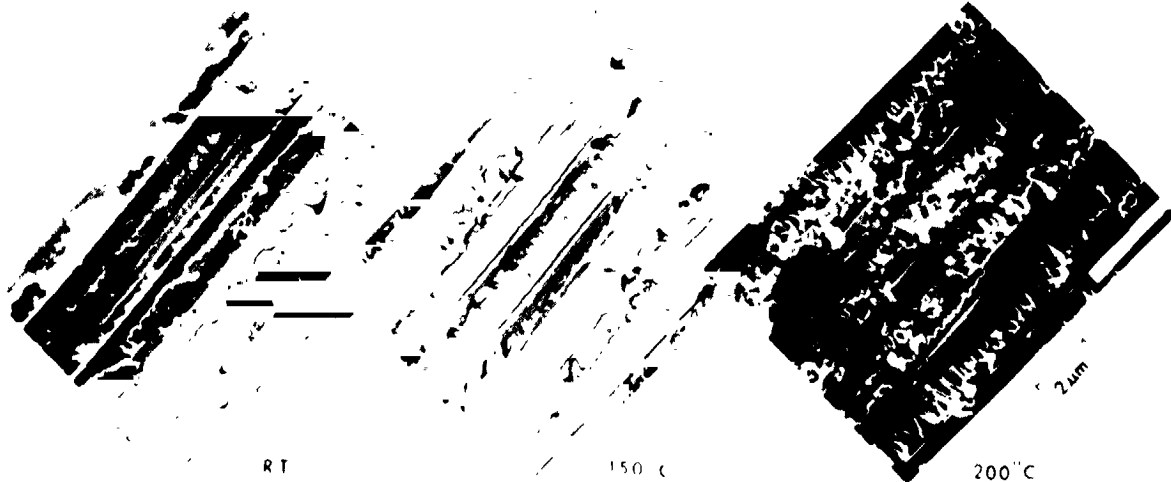
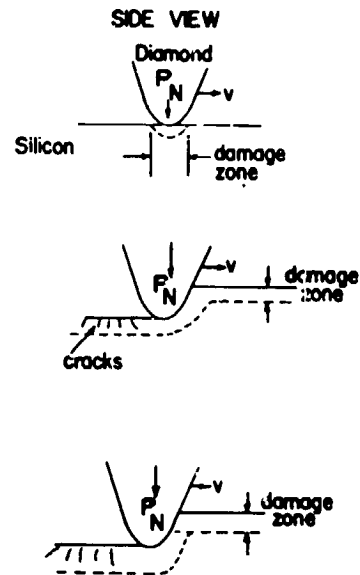
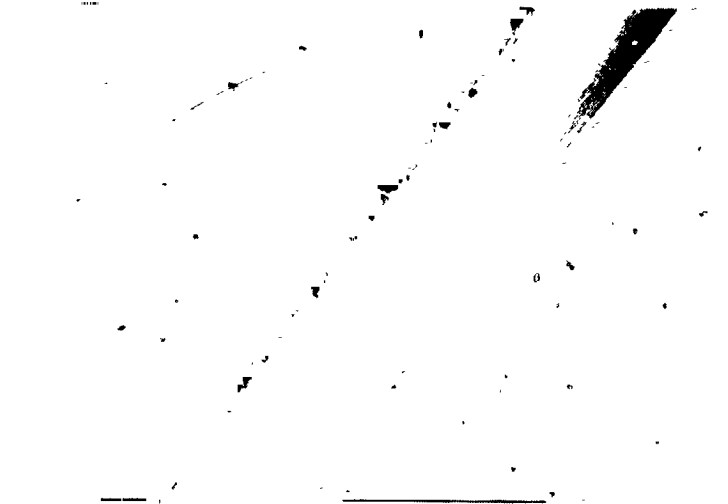


ADVANCED SILICON SHEET

OD Sawing (Dicing)

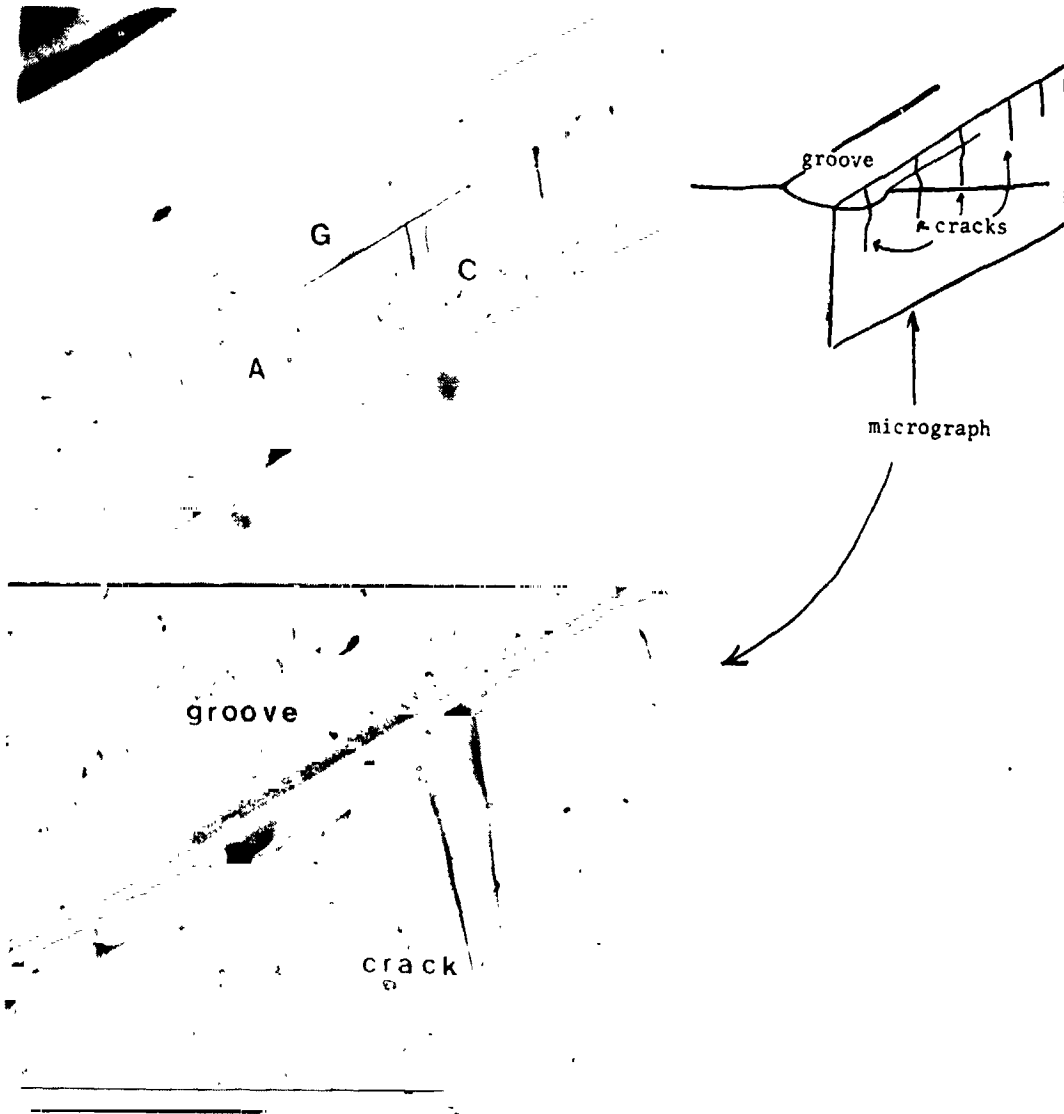


ORIGINAL QUALITY  
OF POLY-SILICON



ADVANCED SILICON SHEET

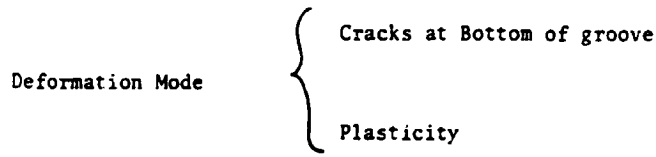
Examples of Cracks at the Bottom of Grooves



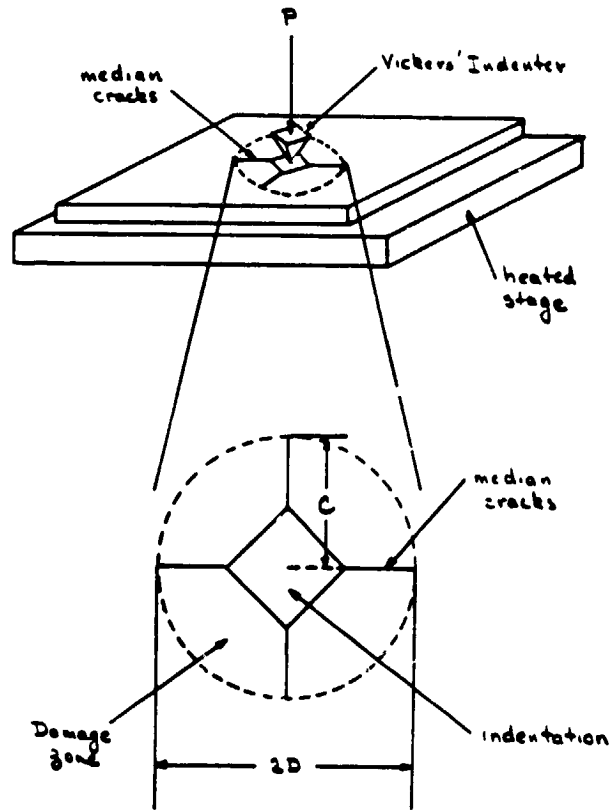
ORIGINAL PAGE IS  
OF POOR QUALITY

# ADVANCED SILICON SHEET

## Summary of High-Speed, Elevated Cutting



Fluids, Temperature--- influence surface morphology



ADVANCED SILICON SHEET

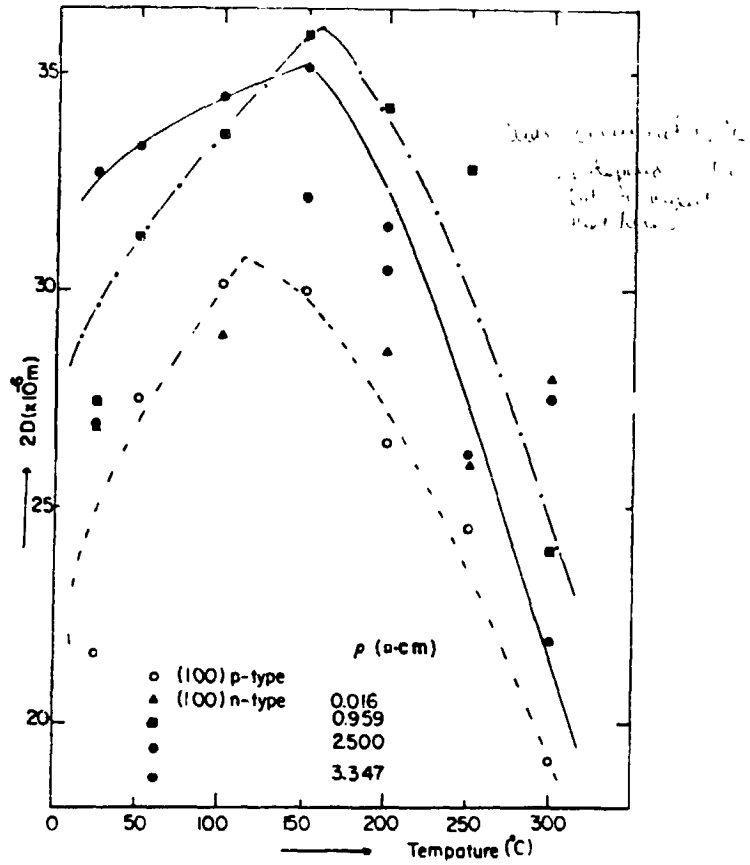
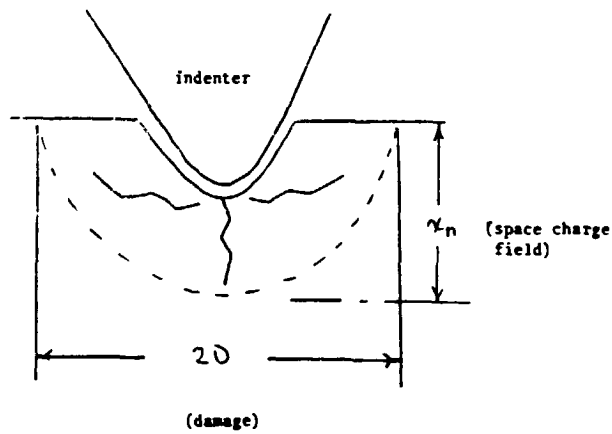


Figure 36. Damage size(2D) vs. indentation temperature for p-type and n-type Cz silicon. The indentation load was 0.49N. The n-type silicon had resistivities of 0.016, 0.959, 2.5, and 3.347Ωcm.

Indentation Model



|                  |
|------------------|
| $2D \propto X_n$ |
|------------------|

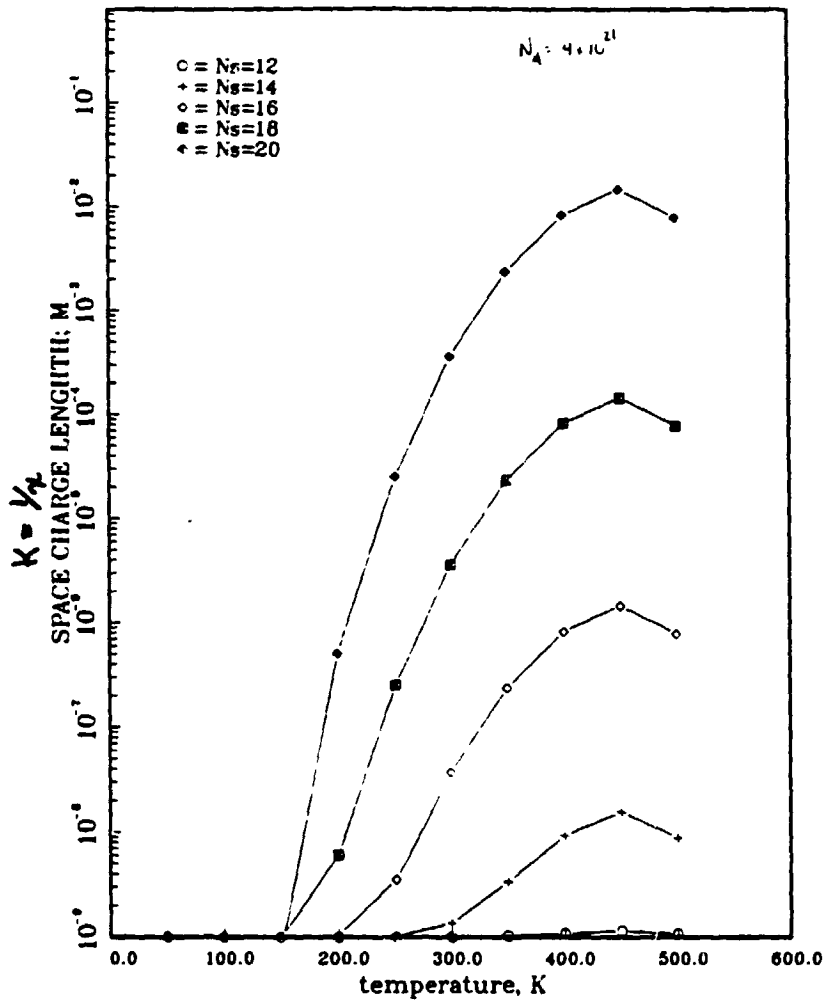
at low P, space charge fields influence damage

$$X_n = \frac{N_s}{N_D} \left[ \frac{e \frac{(\mu_e - E_{SS})}{kT}}{1 + e \frac{(\mu_e - E_{SS})}{kT}} - 1 \right]$$

- \* $N_s$  - finite number of surface states
- \* $N_s, E_{SS}$  not known but extracted from expt.
- \* $\mu_e$ , electrochemical potential

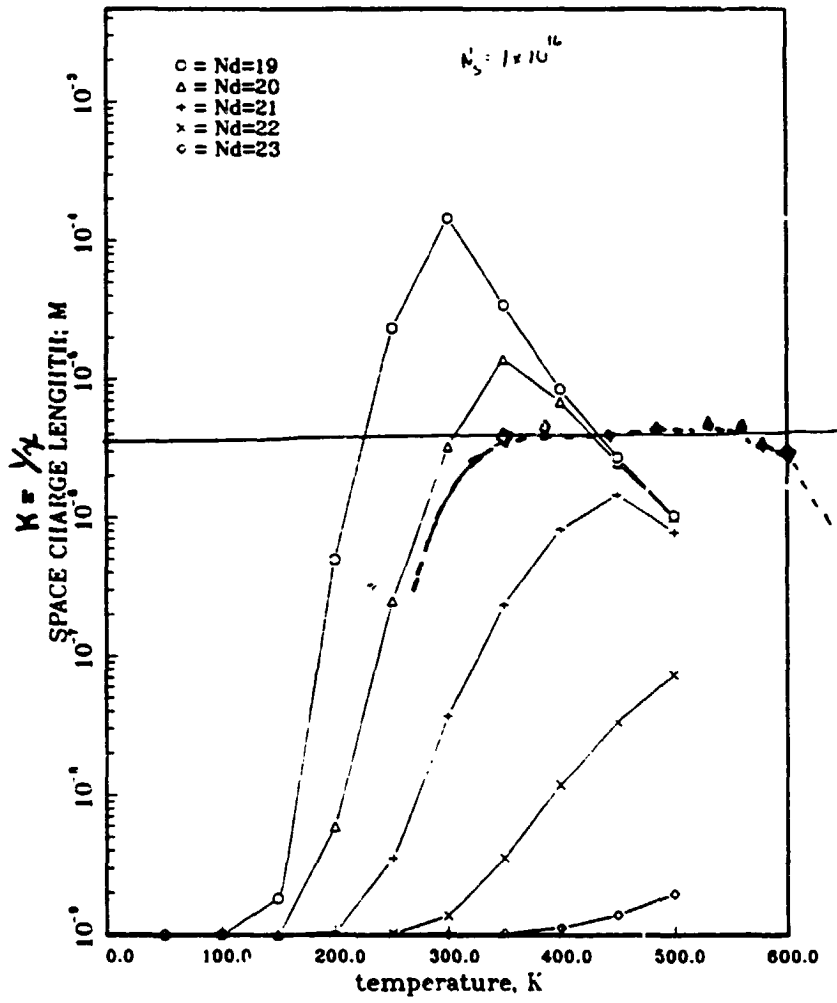
$$2D = f(N_D, N_s, E_{SS}, T)$$

Space Charge Length as a Function of Temperature





Space Charge Length as a Function of Temperature



# ADVANCED SILICON SHEET

## Summary of Indentation Model

2D and  $x_n$  exhibit maximum at 150C

$$N_s = 10^{16} - 10^{18} / m^2$$

$$E_s = 0.79 \text{ eV}$$

Doping level influences 2D

Predict  $T, N_D$  variation with 2D

## Summary of Silicon Results

### . Wear rate

. Ethanol - highest

. air - lowest

### . Damage

.load — plasticity, p 100gf  
          — cracks, p 200gf

### .temp

cracks, damage decreases  
at T 250°C

. bulk doping

. fluid

## Conclusions

### Mechanisms of Wear

- . Wear rate and damage includes: cracks and plasticity
- . Laboratory simulation tests provide guidance in modifying industrial practices.
- . Wear rate may be optimized and damage may be minimized

Load (below 0.98N (100fg)  
Fluid (alcohol-based vs. water-based fluids)  
Temp (200-300°C)

- . Model allows parameters to be identified and range to be extrapolated.
- . Unresolved problems: Impact, fatigue

## Residual Stresses

- . Interferometry is a promising NDT technique for sheet geometries
- . Edges - compressive  
Center - tensile
- . EFG -  $v_{\text{growth}} = 2 \text{ cm/min} - \sigma_{\text{RS}} = \pm 10 \text{ MPa}$   
WEB -  $v_{\text{growth}} = \text{ cm/min} - \sigma_{\text{RS}} = \pm 1 \text{ MPa}$
- . Unresolved problems: anisotropy of E,  $\nu$   
dendrite geometry